

# HMHL065N170CI DFN 8x8 Integrated Cascode GaN

## Description

HMHL065N170CI is an integrated D-mode Cascode GaN power transistor which possesses benefits of Cascode GaN and modified switching performance. HMHL065N170CI provides high breakdown voltage, high current and high operating speed which is suitable for high power applications.

## Key Specifications

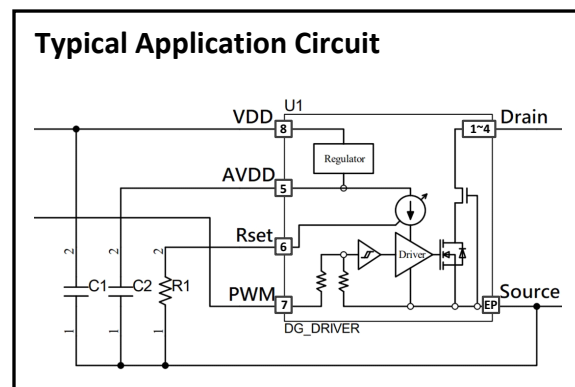
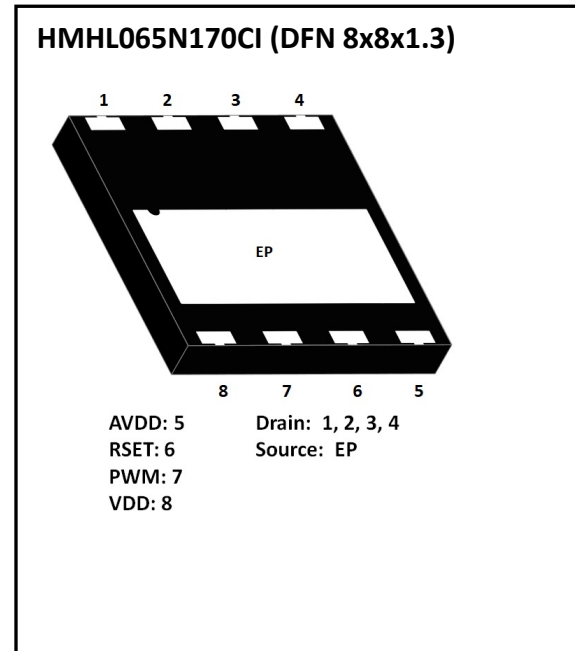
Part Number	HMHL065N170CI
V <sub>DSS</sub> , min.	650V
V <sub>(TR)DSS</sub> , min.	800V
R <sub>DS(ON)</sub> , typ.	170mΩ
Package	DFN 8 x 8 mm

## Features

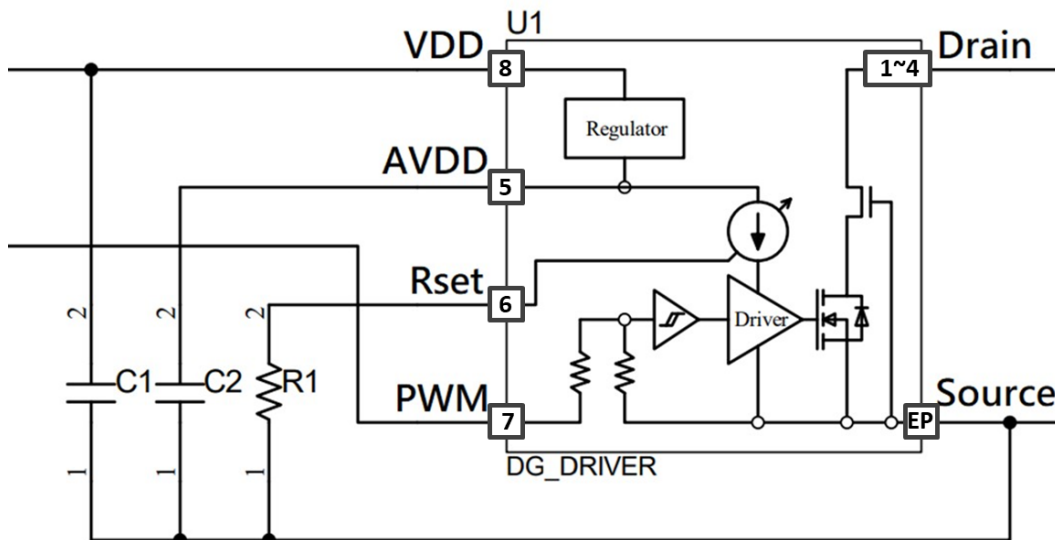
- Gate drive voltage compatibility (up to 30V)
- High operating frequency
- Zero reverse recovery loss
- Wide V<sub>cc</sub> Range (10V~30V)
- 5 V / 15 V input-compatible
- Programmable turn-on dv/dt
- 1 MHz operation

## Applications

- Switch Mode Power Supplies (SMPS)
- AC-DC/ DC-DC Converters
- Motor Drives



## 1- Pin Description



Pin No.	Symbol	Description
1~4	Drain	Connect to the drain terminal of Cascode GaN
5	$AV_{DD}$	Gate driver supply voltage.
6	$R_{SET}$	dv/dt setting pin.
7	PWM	PWM input.
8	$V_{DD}/V_{in}$	Supply voltage
EP	Source	Connect to the source terminal of Cascode GaN

## 2- Electrical Characteristics

➤ Table 1 Absolute maximum ratings

Symbol	Parameter	Value	Unit
$V_{DSS}$	Drain-source voltage	650	V
$V_{(TR)DSS}$	Transient drain to source voltage <sup>a</sup>	800	V
$V_{DD}$	Supply Voltage	40	V
$V_{PWM}$	PWM Voltage	30	V
$V_{AVDD}$	Internal Operating Voltage	7	V
$V_{RSET}$	Slew rate setting Voltage	7	V
$P_{tot}$	Total power dissipation @ $T_C = 25^\circ C$	60	W

I <sub>D</sub>	Drain current (continuous) at T <sub>c</sub> = 25°C operation		8	A
	Drain current (continuous) at T <sub>c</sub> = 100°C operation		5	A
I <sub>DM</sub>	Pulsed drain current (pulse width: 100 μs)		13	A
T <sub>c</sub>	Operating temperature	Case	-55 to +150	°C
T <sub>J</sub>		Junction	-55 to +150	°C
T <sub>S</sub>	Storage temperature		-55 to +150	°C
T <sub>SOLD</sub>	Soldering peak temperature <sup>b</sup>		260	°C

a. In off-state, spike duty cycle D<0.01, spike duration <1 μs

b. For 10 sec., 1.6mm from the case

➤ **Table 2 Thermal Characteristics**

Symbol	Parameter	Value	Unit
R <sub>θJA</sub>	Thermal resistance junction-ambient	38	°C/W
R <sub>θJC</sub>	Thermal resistance junction-case	2.0	°C/W

➤ **Table 3 Electrical Characteristics**

$V_{in}=15V$ ,  $V_{ds}=400V$ ,  $F_{sw}=1MHz$ ,  $R_{set}=10k\Omega$ ,  $T_{CASE} = 25\text{ }^{\circ}C$  unless otherwise stated

Symbol	Parameter	Conditions	Values			Unit
			min.	typ.	max.	
$V_{(BL)DSS}$	Drain-source voltage	$V_{GS}=0V$	650	-	-	V
$V_{DD}$	VIN Operating Voltage		8		30	V
$I_Q$	VIN Quiescent Current	$V_{PWM}=0V$		0.1	0.3	mA
$I_Q$	VIN Operating Current	$F_{SW}=500kHz$ , $C_{OUT}=100pF$		1	3	mA
$V_{AVDD}$	Internal Operating Voltage		4.8	5.0	5.2	V
$V_{PWMH}$	PWM Logic High Threshold				4	V
$V_{PWML}$	PWM Logic Low Threshold		1			V
$V_{PWM\_HYS}$	PWM Input Logic Hysteresis			3		V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS}=10V$ , $I_D=5A$ , $T_J=25\text{ }^{\circ}C$	-	170	240	m $\Omega$
		$V_{GS}=10V$ , $I_D=5A$ , $T_J=150\text{ }^{\circ}C$	-	330	-	
$I_{DSS}$	Drain-source leakage current	$V_{GS}=0V$ , $V_{DS}=650V$ , $T_J=25\text{ }^{\circ}C$	-	2.2	12	$\mu$ A
		$V_{GS}=0V$ , $V_{DS}=650V$ , $T_J=150\text{ }^{\circ}C$	-	100	-	
$t_{D(on)}$	Turn-On Propagation Delay	PWM=0 to 5V	-	15	-	ns
$t_{D(off)}$	Turn-Off Propagation Delay	PWM=0 to 5V	-	25	-	
$T_R$	Drain Rise Time	PWM=0 to 5V		5		ns
$T_F$	Drain Fall Time	PWM=0 to 5V		5		ns
$F_{SW}$	Switching Frequency				1	MHz
$t_{PW}$	Pulse Width		0.05			us
$Q_{RR}$	Reverse recovery charge	$V_{GS}=-10V$ , $V_{DS}=0V$	-		-	nC

## Recommended Operating Conditions

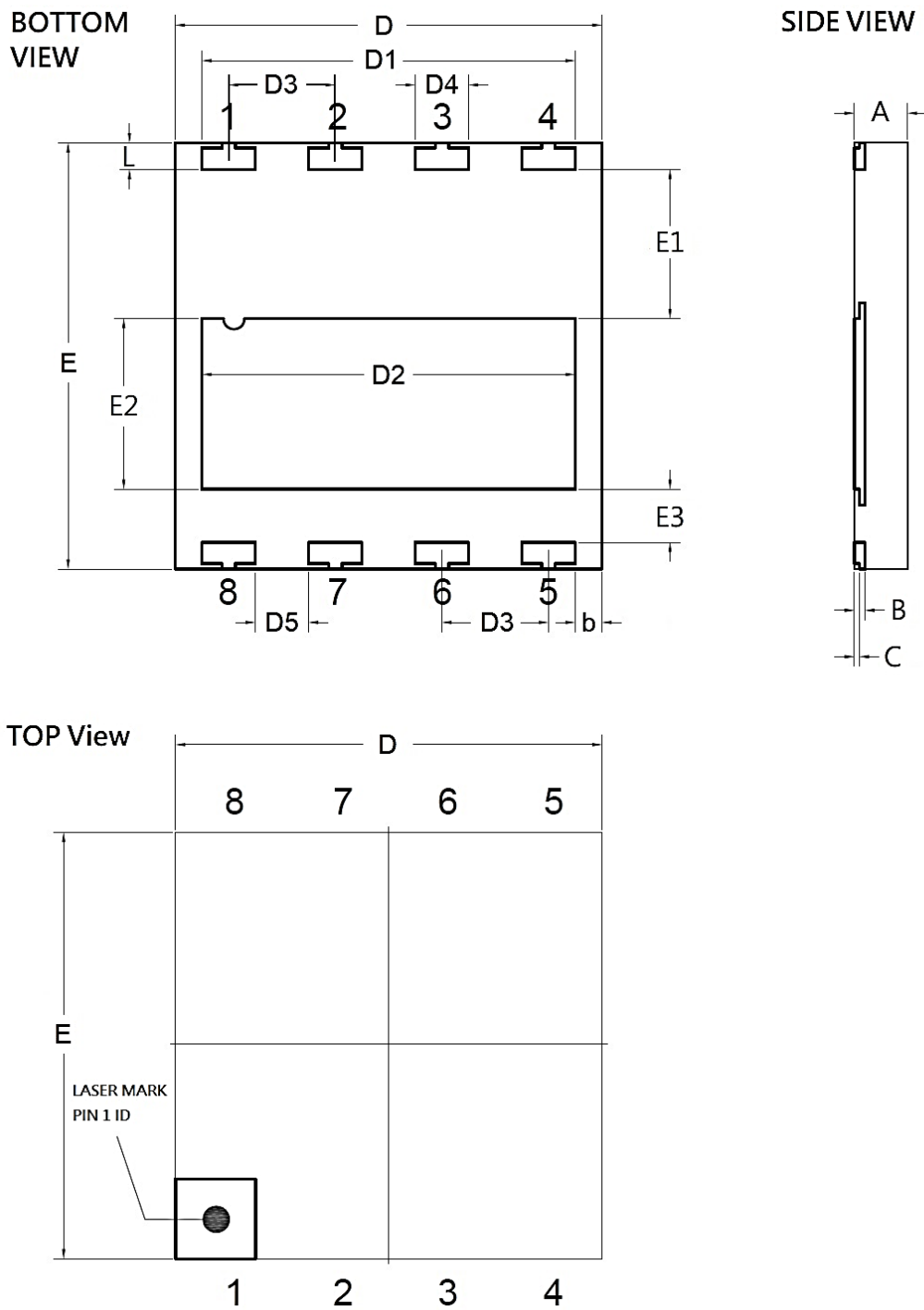
Parameter	Symbol	Value	Unit
Supply Voltage	$V_{DD}$	10~30	V
PWM Voltage	$V_{PWM}$	5/15	V
Internal Operating Voltage	$V_{AVDD}$	5.6	V
Slew rate setting resistor	$R_{SET}$	10K~100K	$\Omega$
Operating Ambient Temperature	$T_{OP}$	-40~125	$^{\circ}C$

## Recommended Component Values

The following table shows the recommended component values for the external  $C_{VDD}$ ,  $R_{PWM}$ ,  $C_{PWM}$ ,  $C_{AVDD}$ , and  $R_{SET}$ . These components should be placed as close as possible to the power device.

Parameter	Symbol	Min	Typ	Max	Unit
VDD capacitor	CVDD		0.1		$\mu F$
VAVDD capacitor	CAVDD		0.022		$\mu F$
Gate driver turn-on current set resistor	RSET	10		100	K $\Omega$
PWM filter resistor	RPWM		100		$\Omega$
PWM filter capacitor	CPWM		100		pF

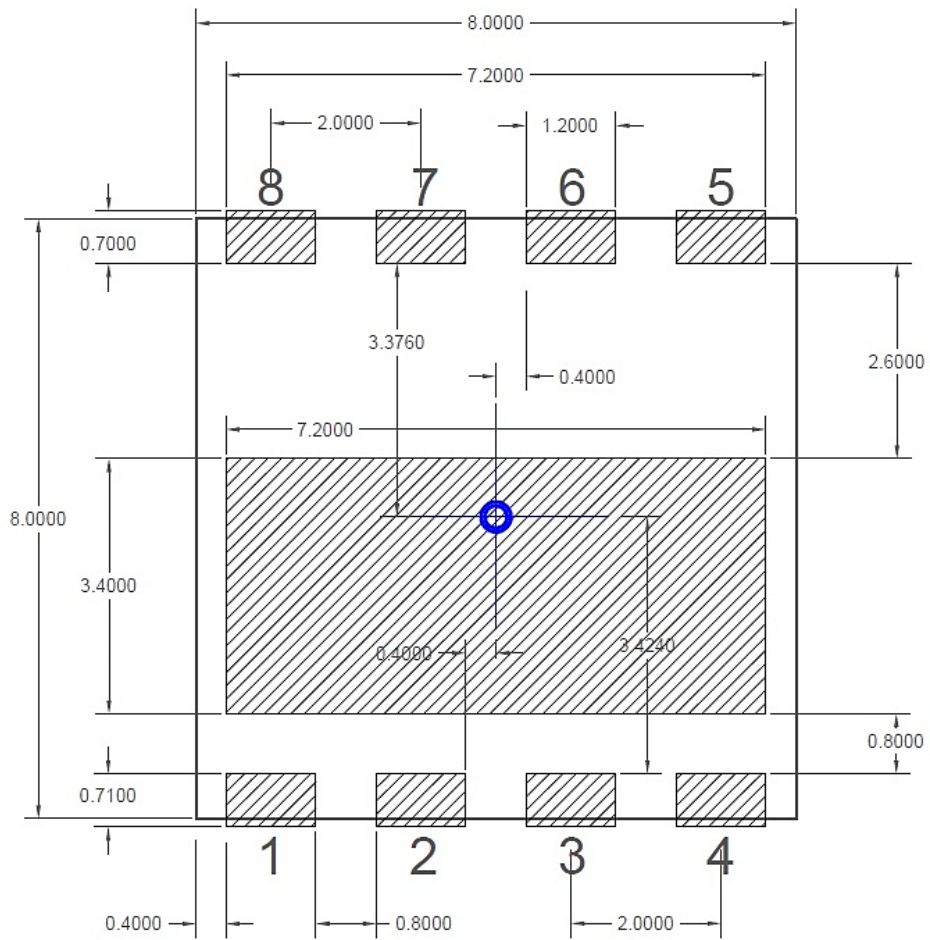
### 3- Package Outline Dimensions



➤ Table 4 Dimension

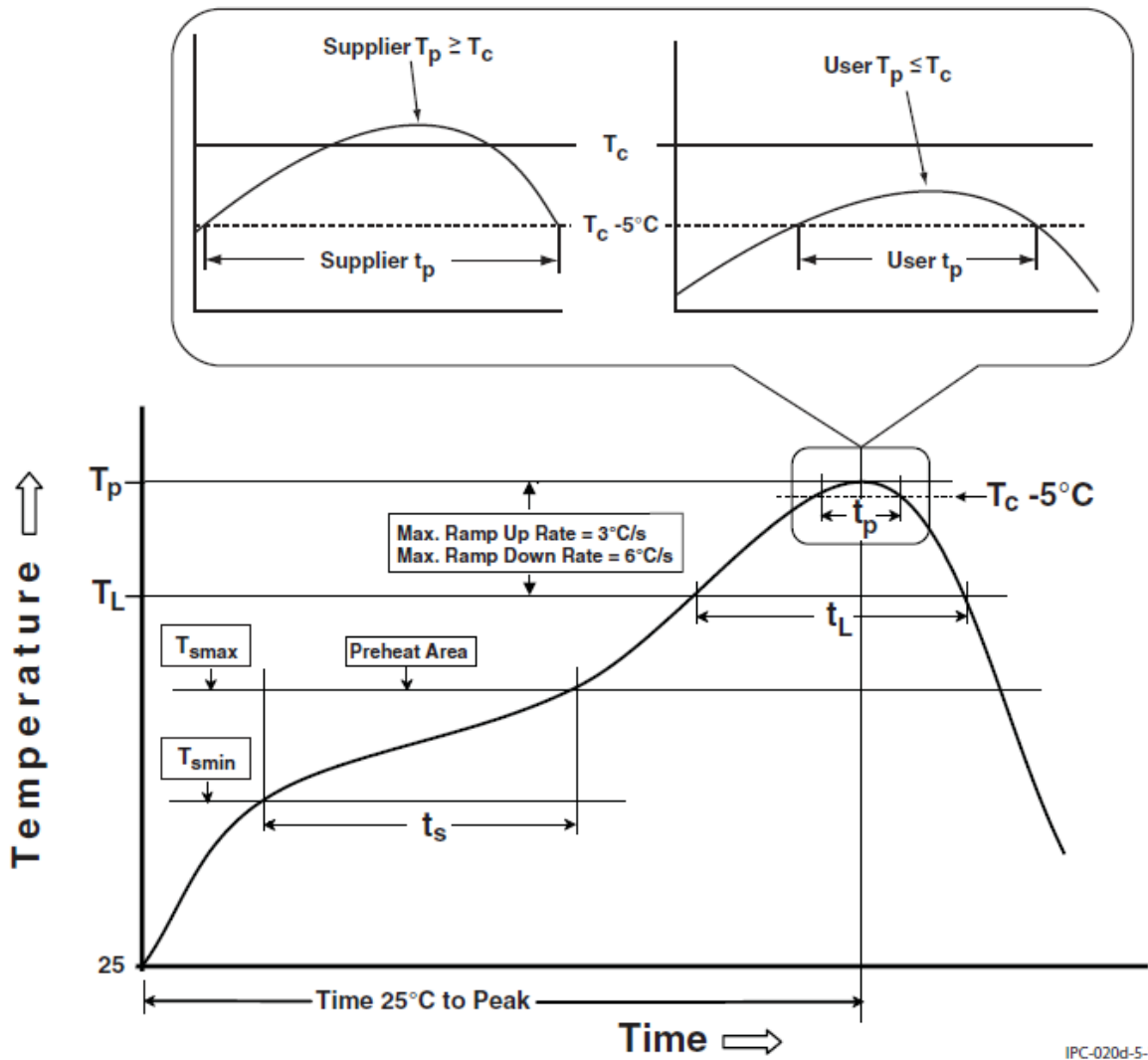
SYMBOL	DIMENSION (IN MM)			SYMBOL	DIMENSION (IN MM)		
	MINIMUM	MOMINAL	MAXIMUM		MINIMUM	MOMINAL	MAXIMUM
A	1.20	1.30	1.40	-	-	-	-
B	--	0.203	--	-	-	-	-
C	--	0.100	--	-	-	-	-
D	7.90	8.00	8.10	E	7.90	8.00	8.10
D1	6.90	7.00	7.10	E1	2.70	2.80	2.90
D2	6.90	7.00	7.10	E2	3.10	3.20	3.30
D3	2.00 BSC			E3	0.90	1.00	1.10
D4	0.95	1.00	1.05	L	0.40	0.50	0.60
D5	0.95	1.00	1.05	-	-	-	-
b	0.40	0.50	0.60	-	-	-	-

## DFN-8X8 Recommended PCB Soldering Footprint





# Reflow Soldering Profile



IPC-020d-5-1